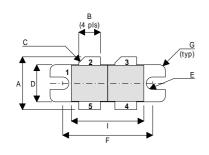
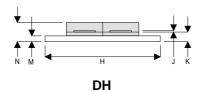


ROHS COMPLIANT METAL GATE RF SILICON FET

MECHANICAL DATA





PIN 1	SOURCE (COMMON)	PIN 2	DRAIN 1
PIN 3	DRAIN 2	PIN 4	GATE 2

PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
Α	13.97	0.26	0.550	0.010
В	5.72	0.13	0.225	0.005
С	45°	5°	45°	5°
D	9.78	0.13	0.385	0.005
Е	1.65R	0.13	0.065R	0.005
F	23.75	0.13	0.935	0.005
G	1.52R	0.13	0.060R	0.005
Н	30.48	0.13	1.200	0.005
1	19.17	0.26	0.755	0.010
J	0.13	0.02	0.005	0.001
K	2.54	0.13	0.100	0.005
М	1.52	0.13	0.060	0.005
N	5.08	0.50	0.200	0.020

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 100W - 28V - 500MHz**PUSH-PULL**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 10 dB MINIMUM

APPLICATIONS

 HF/VHF/UHF COMMUNICATIONS from 1 MHz to 500 MHz

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

$\overline{P_D}$	Power Dissipation	290W
BV _{DSS}	Drain – Source Breakdown Voltage *	70V
BV_GSS	Gate – Source Breakdown Voltage *	±20V
I _{D(sat)}	Drain Current *	15A
T _{stg}	Storage Temperature	−65 to 150°C
Tj	Maximum Operating Junction Temperature	200°C

^{*} Per Side

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit
	PER SIDE						
B\/	Drain-Source	V _{GS} = 0	I _D = 100mA	70			V
BV _{DSS}	Breakdown Voltage	VGS = 0	ID = IOOIIIA	70			V
	Zero Gate Voltage	1/ 201/				3	A
IDSS	S Drain Current $V_{DS} = 28V$ $V_{GS} = 0$	v _{GS} = 0			3	mA	
I _{GSS}	Gate Leakage Current	V _{GS} = 20V	V _{DS} = 0			1	μА
V _{GS(th)}	Gate Threshold Voltage*	I _D = 10mA	$V_{DS} = V_{GS}$	1		7	V
9 _{fs}	Forward Transconductance*	V _{DS} = 10V	I _D = 3A	2.4			S
	TOTAL DEVICE						
G _{PS}	Common Source Power Gain	P _O = 100W		10			dB
η	Drain Efficiency	V _{DS} = 28V	$I_{DQ} = 1.2A$	50			%
VSWR	Load Mismatch Tolerance	f = 500MHz		20:1			_
PER SIDE							
C _{iss}	Input Capacitance	$V_{DS} = 28V$	$V_{GS} = -5V f = 1MHz$			180	pF
C _{oss}	Output Capacitance	$V_{DS} = 28V$	$V_{GS} = 0$ $f = 1MHz$			90	pF
C _{rss}	Reverse Transfer Capacitance	$V_{DS} = 28V$	$V_{GS} = 0$ $f = 1MHz$			7.5	pF

^{*} Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 0.6°C / W
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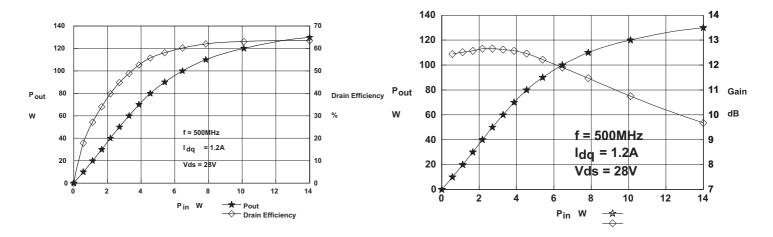


Figure 1 - Power Output and Efficiency vs. Power Input.

Figure 2 - Power Output & Gain vs. Power Input.

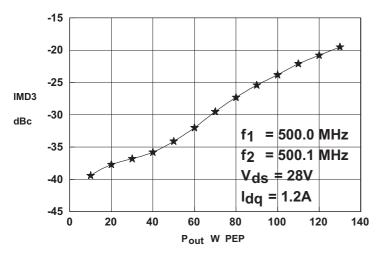


Figure 3 - IMD vs. Output Power.

D1012UK OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z _S Ω	Z_{L}
500	2.0 - j2.2	2.6 - j0.6

N.B. Impedances measured terminal to terminal

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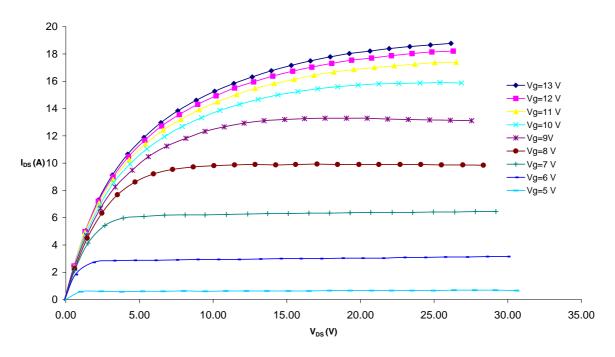


Figure 4 – Typical IV Characteristics.

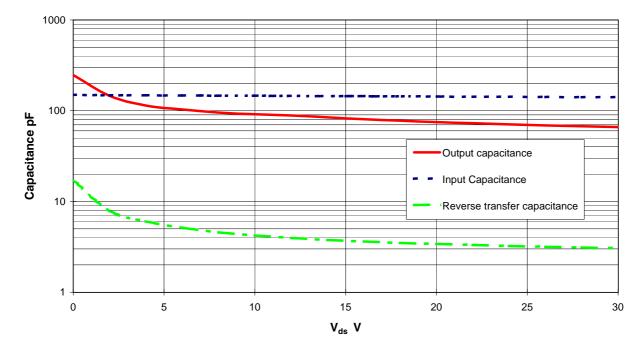


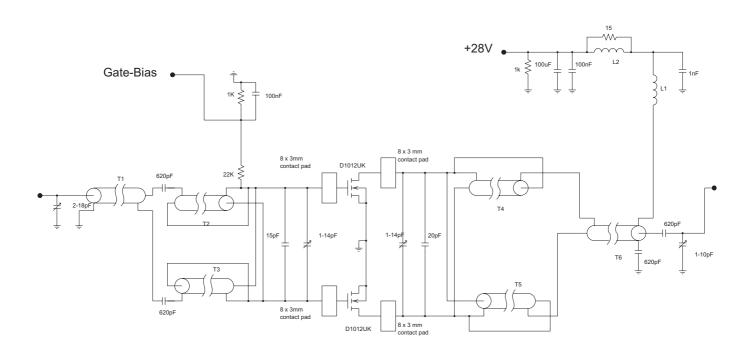
Figure 5 – Typical CV Characteristics.

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D1012UK 500MHz TEST FIXTURE

T1.6 50 Ohm UT85 semi-rigid coax 65mm T2,3,4,5 75mm 15 Ohm UT85-15 semi-rigid coax L1 6 turns

21 swg enamelled copper wire, 3mm i.d.

L2 19 swg enamelled copper wire on Fair-Rite FT82-43 core 8.5 turns

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